Product data sheet

1. General description

Ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- · Low forward voltage drop
- Soft recovery characteristic

3. Applications

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- · High frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_R	reverse voltage	DC		-	-	800	V
I _{F(AV)}	average forward current	$δ = 0.5 ; T_h \le 73 °C; SQW; Fig. 1;$ Fig. 2; Fig. 3	[1]	-	-	8	Α
I _{FRM}	repetitive peak forward current	$\delta = 0.5 \; ; t_p = 25 \; \mu s; T_h \le 73 \; ^{\circ}C; \; SQW$		-	-	16	Α
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; SIN		-	-	60	Α
	forward current	t _p = 8.3 ms; T _{j(init)} = 25 °C; SIN		-	-	66	Α
Static charact	eristics						
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.07	1.5	V
		I _F = 20 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.75	1.95	V
		I _F = 8 A; T _j = 25 °C		-	-	1.7	V
Dynamic char	acteristics					'	
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 6; Fig. 7		-	60	75	ns

^[1] Neglecting switching and reverse current losses

Ultrafast power diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYR29X-800	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

Ultrafast power diode

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	800	V
V_{RWM}	crest working reverse voltage			-	800	V
V_R	reverse voltage	DC		-	800	V
I _{F(AV)}	average forward current	$δ = 0.5 ; T_h \le 73 °C; SQW; Fig. 1; Fig. 2; Fig. 3$	[1]	-	8	Α
I _{FRM}	repetitive peak forward current	$\delta = 0.5 \; ; t_p = 25 \; \mu s; T_h \le 73 \; ^{\circ}C; \; SQW$		-	16	Α
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; SIN		-	60	Α
	forward current	$t_p = 8.3 \text{ ms; } T_{j(init)} = 25 \text{ °C; SIN}$		-	66	Α
T _{stg}	storage temperature			-40	150	°C
Tj	junction temperature			-	150	°C

[1] Neglecting switching and reverse current losses

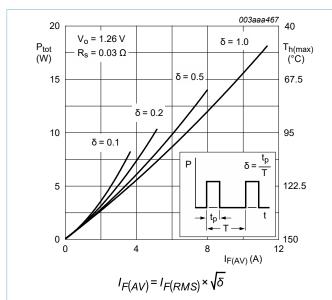


Fig. 1. Forward power dissipation and permissible heatsink temperature as a function of average forward current; square waveform; maximum values

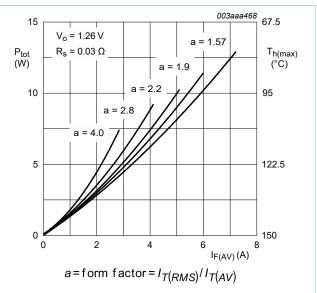
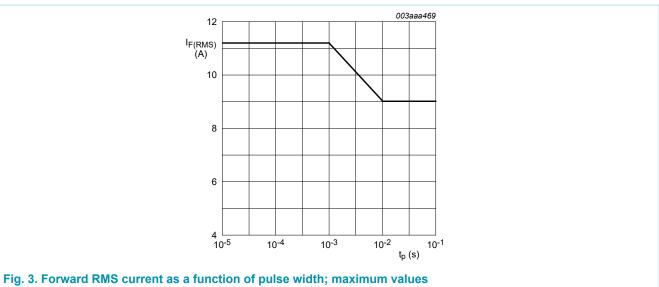


Fig. 2. Forward power dissipation and permissible heatsink temperature as a function of average forward current; sinusoidal waveform; maximum values

Ultrafast power diode



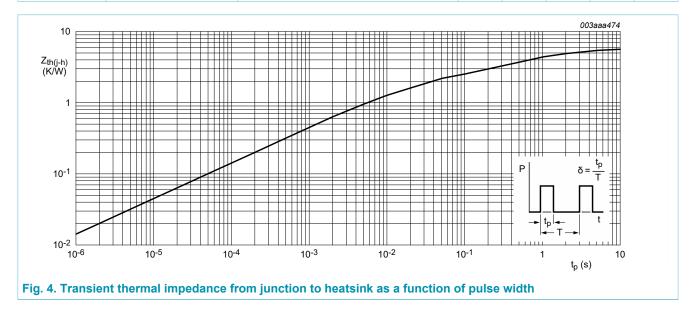
4 / 11

Ultrafast power diode

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 4	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



9. Isolation characteristics

Table 6. Isolation characteristics

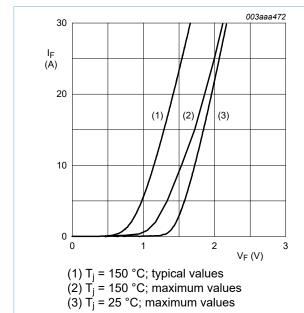
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	pF

Ultrafast power diode

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V_{F}	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.07	1.5	V
		I _F = 20 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.75	1.95	V
		I _F = 8 A; T _j = 25 °C	-	-	1.7	V
I _R	reverse current	V _R = 800 V; T _j = 25 °C	-	1	10	μΑ
		V _R = 800 V; T _j = 100 °C	-	0.1	0.2	mA
Dynamic ch	naracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 6; Fig. 7	-	60	75	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; \underline{\text{Fig. 6}}; \underline{\text{Fig. 8}}$	-	-	6	A
Q _r	recovered charge	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/s}$; $T_j = 25 \text{ °C}$; Fig. 9; Fig. 6	-	150	200	nC
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 10 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 10	-	5	-	V





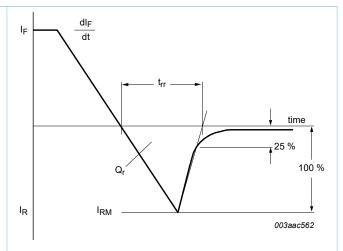


Fig. 6. Reverse recovery definitions; ramp recovery

6 / 11

Ultrafast power diode

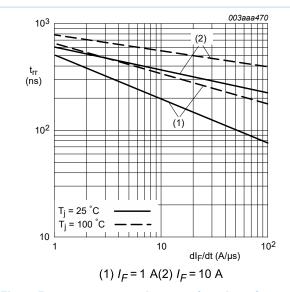


Fig. 7. Reverse recovery time as a function of rate of change of forward current at indicated temperatures; maximum values

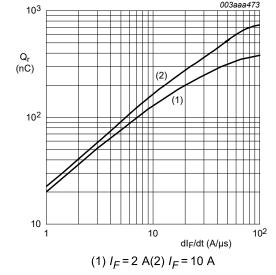


Fig. 9. Recovered charge as a function of rate of change of forward current

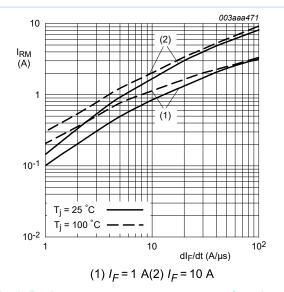


Fig. 8. Peak reverse recovery current as a function of rate of change of forward current at indicated temperatures

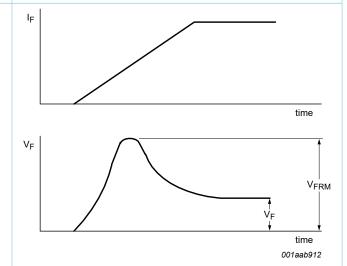


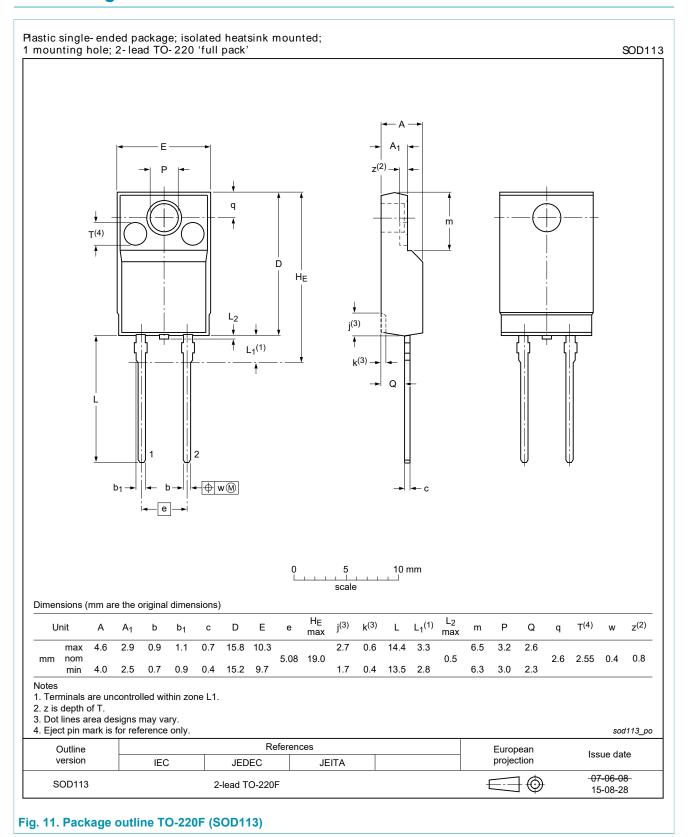
Fig. 10. Forward recovery definitions

WeEn Semiconductors

BYR29X-800

Ultrafast power diode

11. Package outline



Ultrafast power diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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13. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Limiting values	3
8.	Thermal characteristics	5
9.	Isolation characteristics	5
10	. Characteristics	6
11	. Package outline	8
12	. Legal information	9

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